NSN 5961-00-324-1849

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View Online at https://aerobasegroup.com/nsn/5961-00-324-1849 **Inclosure Material:** Metal **Overall Length:** 0.390 inches **Overall Diameter:** 0.406 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 breakdown voltage, collector-to-base, emitter open and 80.0 breakdown voltage, collector-to-emitter, base open and 5.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 1.00 amperes source cutoff current and 2.00 amperes source cutoff current **Power Rating Per Characteristic:** 30.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnp **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug **Specification Data:** 80131-release5569 professional/industrial association specification Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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